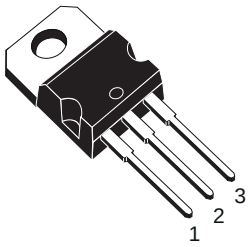
SGS-THOMSON MICROELECTRONICS

STP22NE03L

N - CHANNEL ENHANCEMENT MODE " SINGLE FEATURE SIZE™ " POWER MOSFET

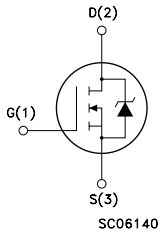
TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STP22NE03L	30 V	< 0.05 Ω	22 A

- TYPICAL $R_{DS(on)}$ = 0.034 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW GATE CHARGE 100 °C
- APPLICATION ORIENTED CHARACTERIZATION



TO-220

INTERNAL SCHEMATIC DIAGRAM



DESCRIPTION

This Power Mosfet is the latest development of SGS-THOMSON unique "Single Feature Size™ " strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalance characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	30	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	30	V
V_{GS}	Gate-source Voltage	± 15	V
I_D	Drain Current (continuous) at T_c = 25 °C	22	A
I_D	Drain Current (continuous) at T_c = 100 °C	16	A
I_{DM}(•)	Drain Current (pulsed)	88	A
P_{tot}	Total Dissipation at T_c = 25 °C	60	W
	Derating Factor	0.4	W/°C
dv/dt	Peak Diode Recovery voltage slope	6	V/ns
T_{stg}	Storage Temperature	-65 to 175	°C
T_j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤22 A, di/dt ≤ 300 A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ T_{JMAX}

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	2.5	$^oC/W$
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	62.5	oC/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.5	$^oC/W$
T_l	Maximum Lead Temperature For Soldering Purpose		300	^oC

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	22	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25\ ^oC$, $I_D = I_{AR}$, $V_{DD} = 15$ V)	TBD	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\ ^oC$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu A$ $V_{GS} = 0$	30			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating $T_c = 125\ ^oC$			1 10	µA µA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 15$ V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu A$	1	1.7	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10$V $I_D = 11$ A $V_{GS} = 5$V $I_D = 11$ A		0.034 0.049	0.05 0.06	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	22			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 11$ A	7	13		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25$ V f = 1 MHz $V_{GS} = 0$		680 160 60	950 220 85	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 15 V I_D = 11 A R_G =4.7 Ω V_{GS} = 5 V		15 70	20 100	ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 24 V I_D = 22 A V_{GS} = 5 V		13 6 6	18	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 24 V I_D = 22 A R_G =4.7 Ω V_{GS} = 5 V		13 33 55	18 46 77	ns ns ns

SOURCE DRAIN DIODE

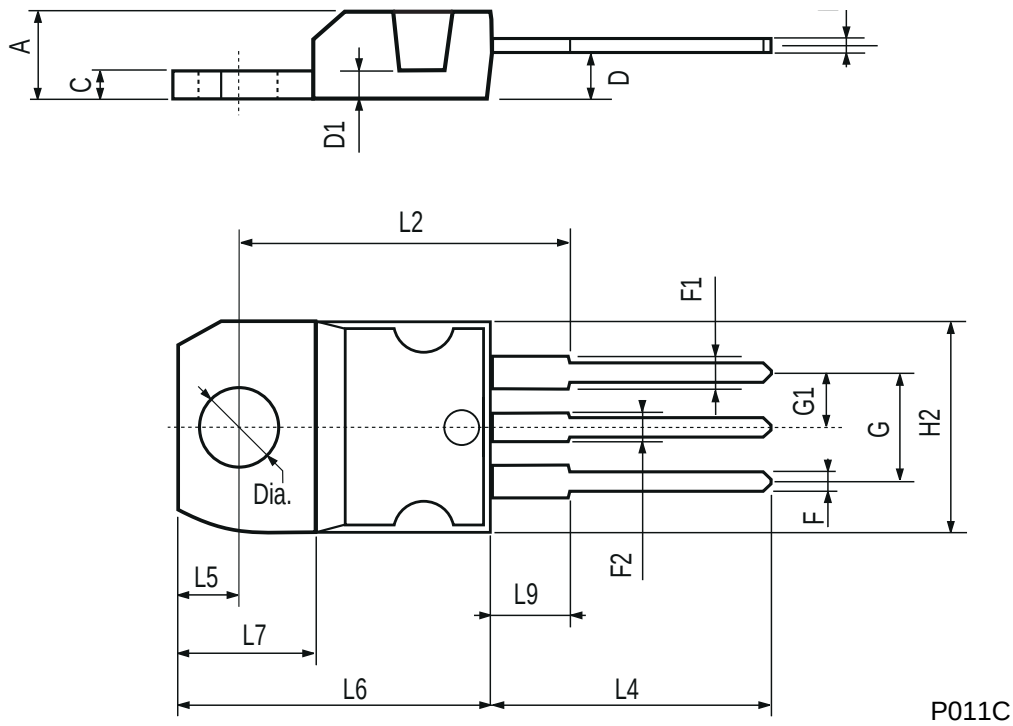
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				22 88	A A
V_{SD} (∗)	Forward On Voltage	I_{SD} = 22 A V_{GS} = 0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 22 A di/dt = 100 A/µs V_{DD} = 15 V T_j = 150 °C		40 44 2.2		ns µC A

(∗) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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